

**Features**

- SiC MOSFET Technology
- High Blocking Voltage with Low On-resistance
- Low Capacitance
- Moisture Sensitivity Level 3
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant (Note 2)("P" Suffix Designates RoHS Compliant. See Ordering Information)

**Maximum Ratings**

- Operating Junction Temperature Range : -55°C to +175°C
- Storage Temperature Range: -55°C to +175°C
- Typical Thermal Resistance: 1.29°C/W Junction to Case

**Applications**

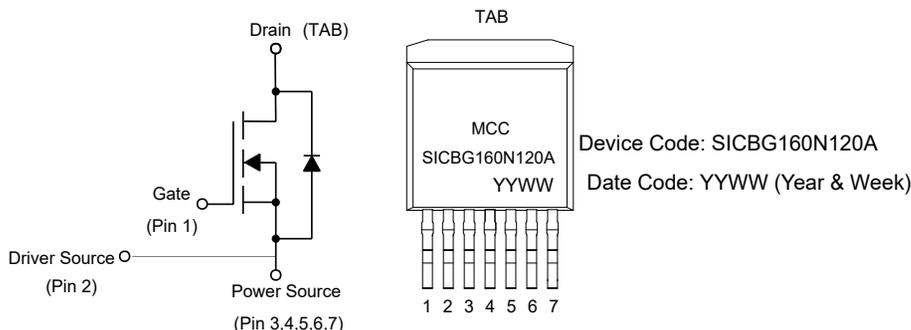
- Solar Inverters
- Switch Mode Power Supplies
- High Voltage DC/DC Converters
- Power Factor Correction (PFC)
- Motor Drives

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	$V_{DS}$	1200	V	
Gate-Source Voltage AC( $f > 1\text{Hz}$ )	$V_{GSmax}$	-5/+22	V	
Gate-Source Voltage Static	$V_{GSop}$	-3/+18	V	
Continuous Drain Current $V_{GS}=18\text{V}$	$I_D$	$T_c=25^\circ\text{C}$	18	A
		$T_c=100^\circ\text{C}$	12	
Pulsed Drain Current (Note 3)	$I_{DM}$	72	A	
Single Pulse Avalanche Energy (Note4)	$E_{AS}$	216	mJ	
Total Power Dissipation	$P_D$	$T_c=25^\circ\text{C}$	116	W
		$T_c=110^\circ\text{C}$	50	

Note:

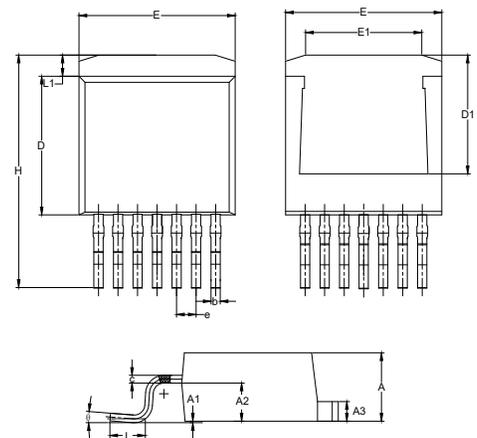
1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. High Temperature Solder Exemptions Applied, see EU Directive Annex 7a.
3. Pulse Test: Pulse Width Limited by  $T_{jmax}$ .
4. EAS Condition:  $T_j=25^\circ\text{C}$ ,  $V_{DD}=50\text{V}$ ,  $V_{GS}=20\text{V}$ ,  $R_g=25\Omega$ ,  $L=10\text{mH}$ ,  $I_{AS}=6.6\text{A}$ .

**Internal Structure**



**N-CHANNEL MOSFET**

**TO-263-7L**



DIM	DIMENSIONS				NOTE
	INCHES		MM		
	MIN	MAX	MIN	MAX	
A	0.167	0.183	4.24	4.64	
A1	0.000	0.010	0.00	0.25	
A2	0.096	0.108	2.45	2.75	
A3	0.045	0.055	1.15	1.40	
b	0.020	0.035	0.50	0.90	
c	0.017	0.024	0.45	0.60	
D	0.347	0.364	8.82	9.25	
D1	0.222		5.65		
E	0.392	0.408	9.96	10.36	
E1	0.256	0.310	6.50	7.89	
e	0.050		1.27		TYP.
H	0.575	0.625	14.61	15.88	
L	0.070	0.110	1.78	2.79	
L1	0.039	0.056	0.98	1.42	
$\theta$	0°	8°	0°	8°	

**Electrical Characteristics @ 25°C (Unless Otherwise Specified)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	1200			V
Gate-Source Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=-5/+22V$			±250	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=1200V, V_{GS}=0V$			10	μA
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=2.5mA$	1.5		3.0	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=20V, I_D=9A$		118	140	mΩ
		$V_{GS}=18V, I_D=9A$		130	160	mΩ
		$V_{GS}=16V, I_D=9A$		150	180	mΩ
Internal Gate Resistance	$R_g$	f=1MHz		4.1		Ω
<b>Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$	$V_{GS}=-3V$		18		A
Diode Forward Voltage	$V_{SD}$	$V_{GS}=-3V, I_{SD}=9A$		4.3		V
Reverse Recovery Time	$t_{rr}$	$V_{GS}=-3/+18V, I_{SD}=9A, V_R=800V, di_F/dt=400A/\mu s$		77.5		ns
Reverse Recovery Charge	$Q_{rr}$		205		nC	
Peak Reverse Recovery Current	$I_{rrm}$		5.3		A	
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=1000V, V_{GS}=0V, f=1MHz, V_{AC}=25mV$		780		pF
Output Capacitance	$C_{oss}$		42			
Reverse Transfer Capacitance	$C_{rss}$		6.2			
Coss Stored Energy	$E_{oss}$		23.6		μJ	
Total Gate Charge	$Q_g$	$V_{DS}=800V, V_{GS}=-3/+18V, I_D=9A$		47		nC
Gate-Source Charge	$Q_{gs}$		8.7			
Gate-Drain Charge	$Q_{gd}$		25			
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=800V, V_{GS}=-3/+18V, R_{G(ext)}=2.5\Omega, I_{DS}=9A, L=600\mu H$		8		ns
Turn-On Rise Time	$t_r$			13		
Turn-Off Delay Time	$t_{d(off)}$			17		
Turn-Off Fall Time	$t_f$			16		
Turn-On switching energy	$E_{on}$			114		μJ
Turn-Off switching energy	$E_{off}$			7		

**Curve Characteristics**

Fig. 1 - Typical Output Characteristic( $T_J=25^\circ\text{C}$ )

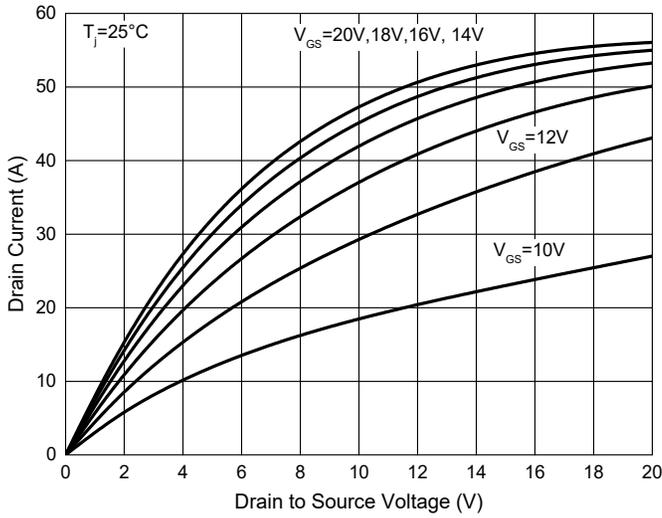


Fig. 2 - Typical Output Characteristic ( $T_J=175^\circ\text{C}$ )

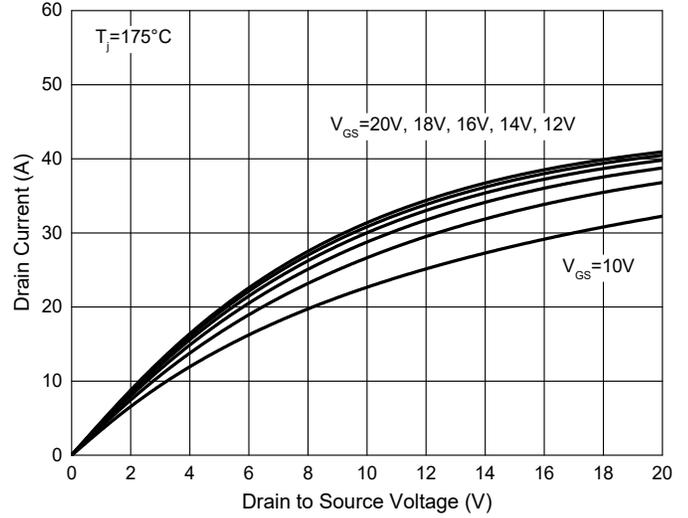


Fig. 3 - Typical Transfer Characteristic

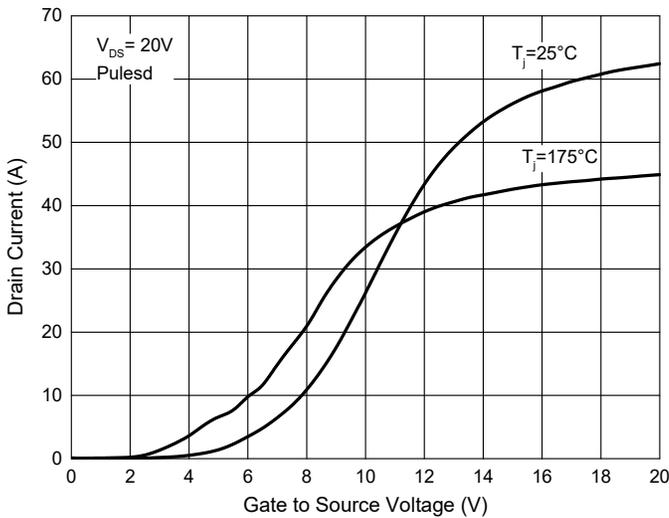


Fig. 4 - On-Resistance vs. Drain Current

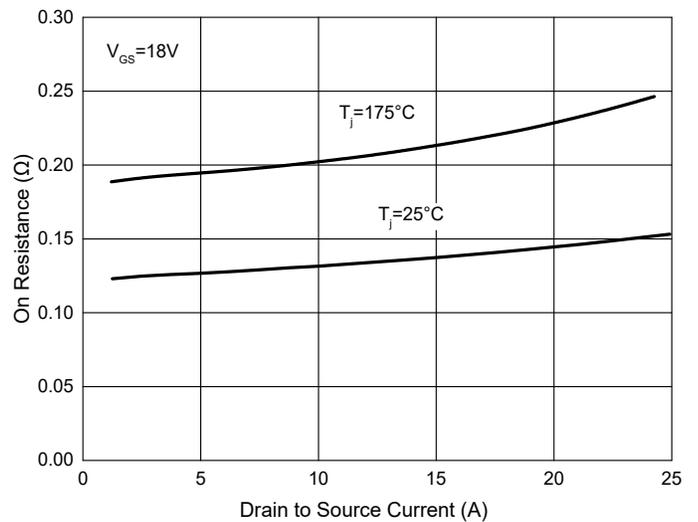


Fig. 5 On-Resistance vs Gate Voltage

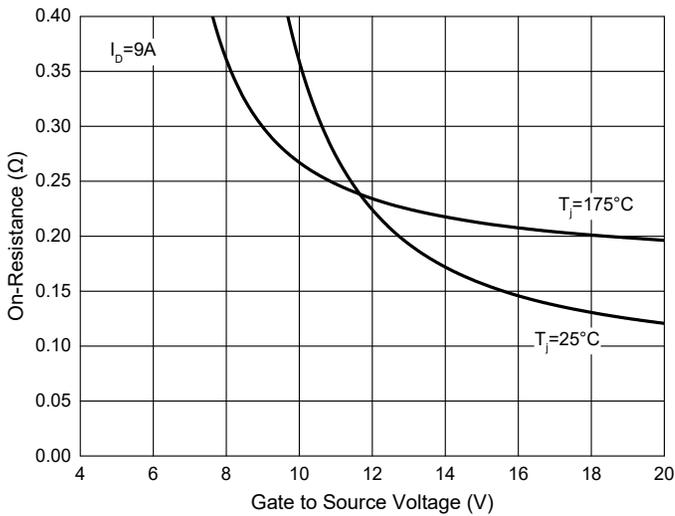
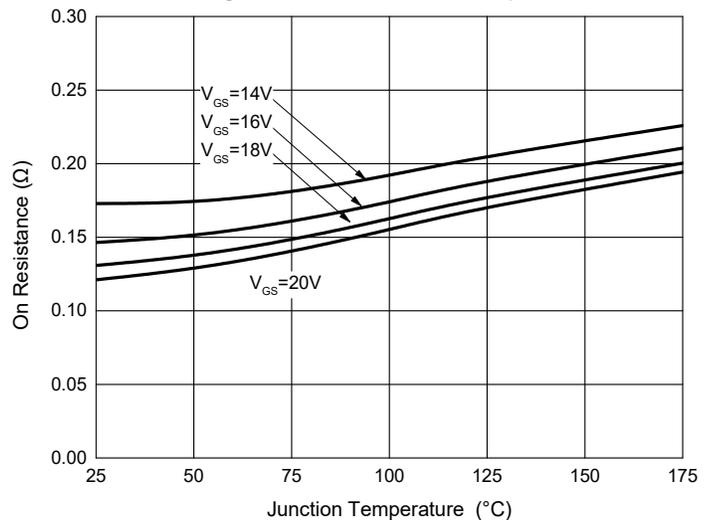


Fig. 6 - On-Resistance vs Temperature



**Curve Characteristics**

Fig. 7 - Normalized On-Resistance vs Temperature

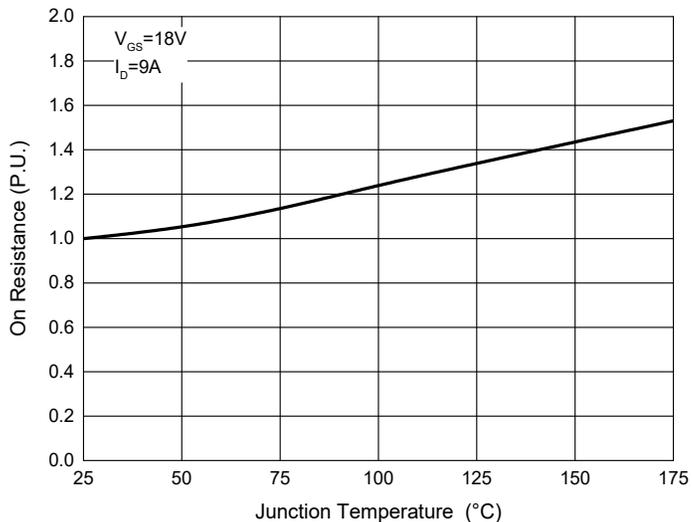


Fig. 8 - Body Diode Characteristic

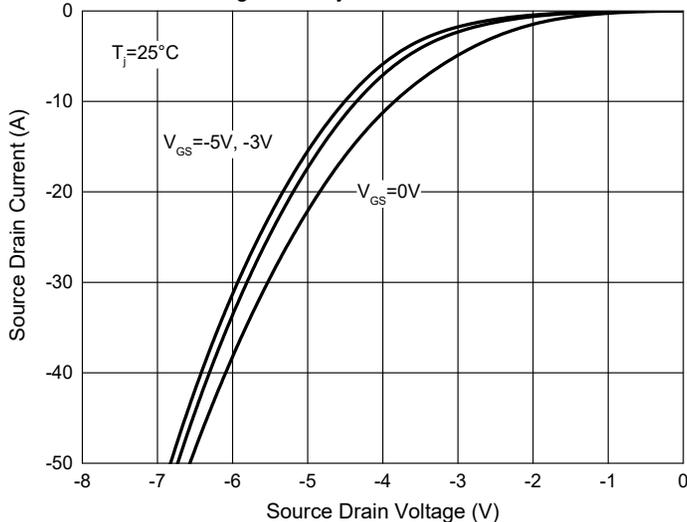


Fig. 9 - Body Diode Characteristic

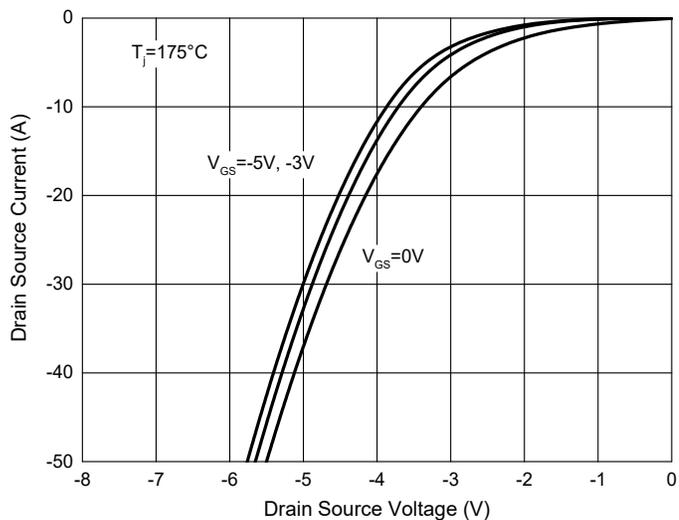


Fig. 10 - Output capacitor stored energy

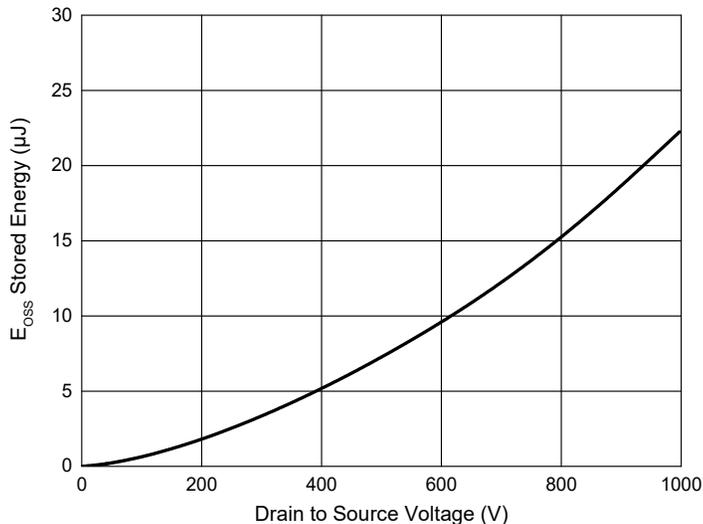


Fig. 11 - Threshold Voltage vs Temperature

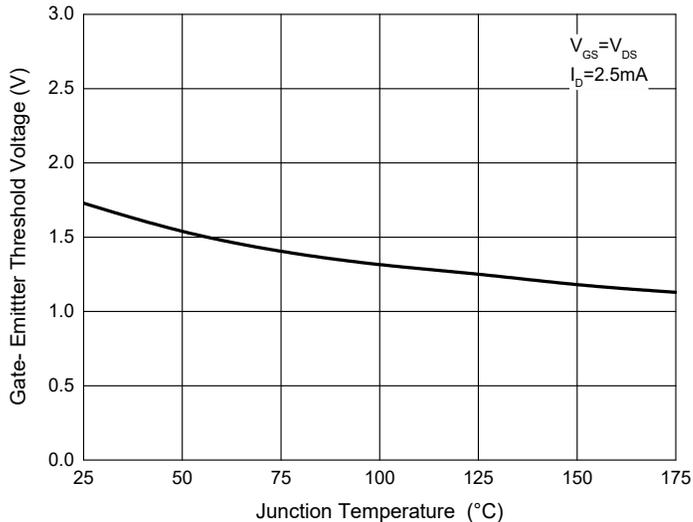
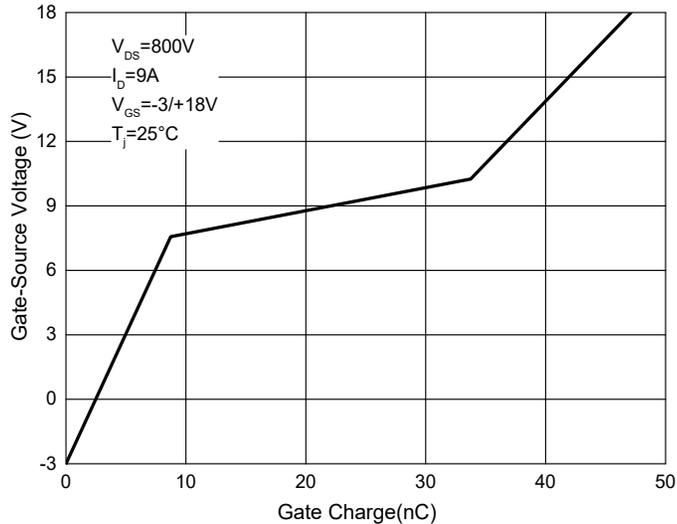


Fig. 12 - Typical Gate Charge



**Curve Characteristics**

Fig. 13 - Capacitance Characteristics

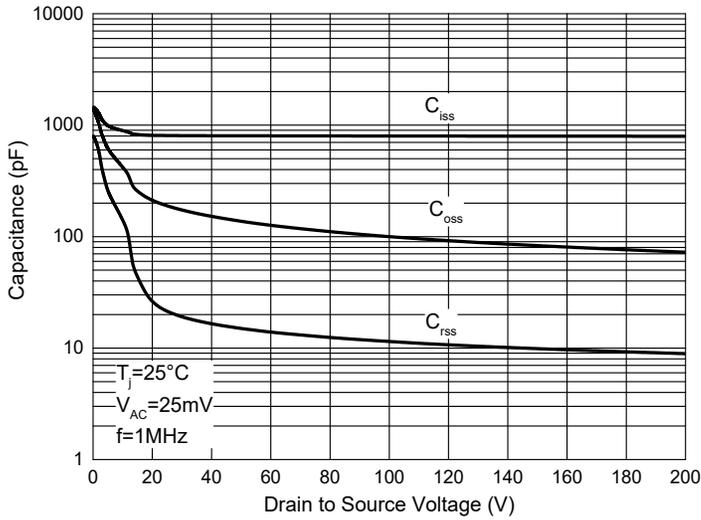


Fig. 14 - Capacitance Characteristics

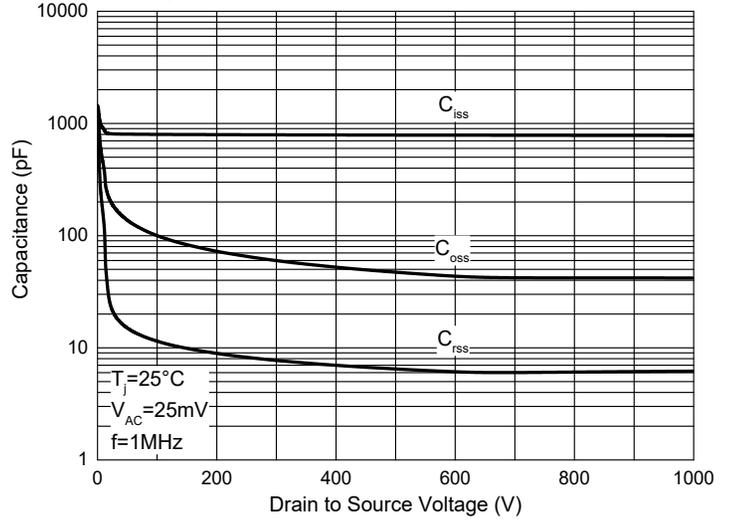


Fig. 15 - Drain Current Derating vs Case Temperature

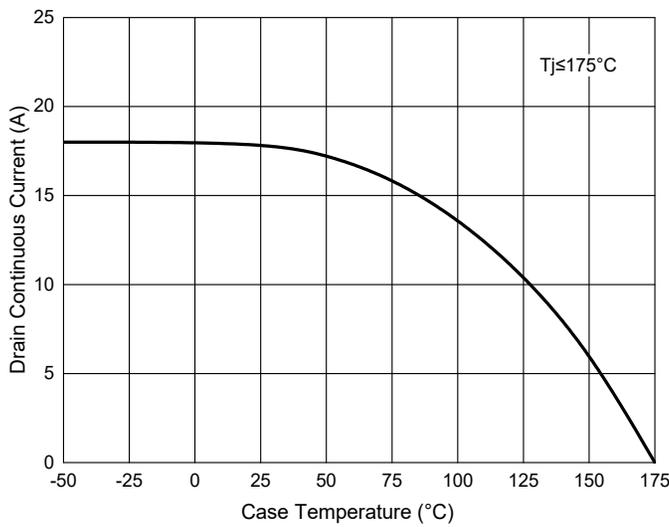


Fig. 16 - Junction to Case Transient Thermal Impedance

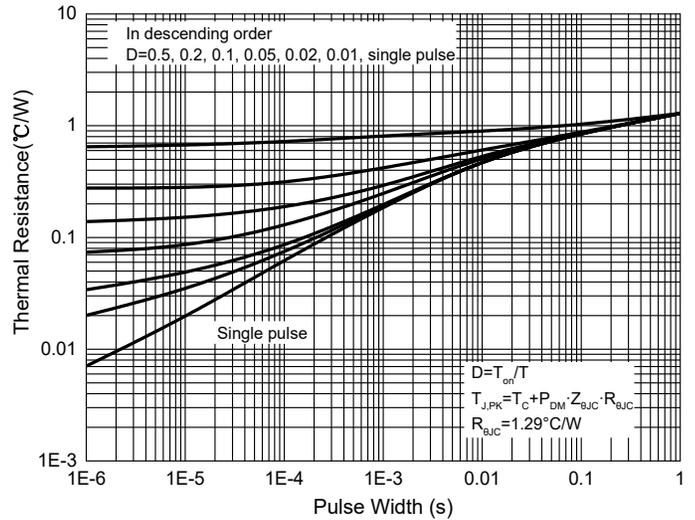


Fig. 17 - Safe Operation Area

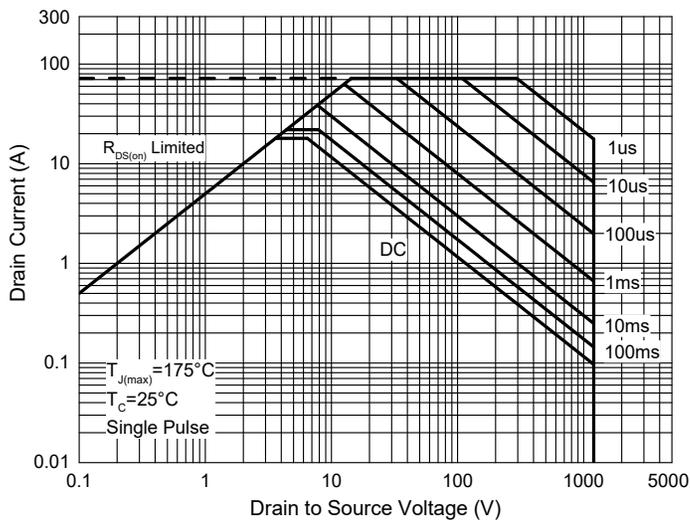
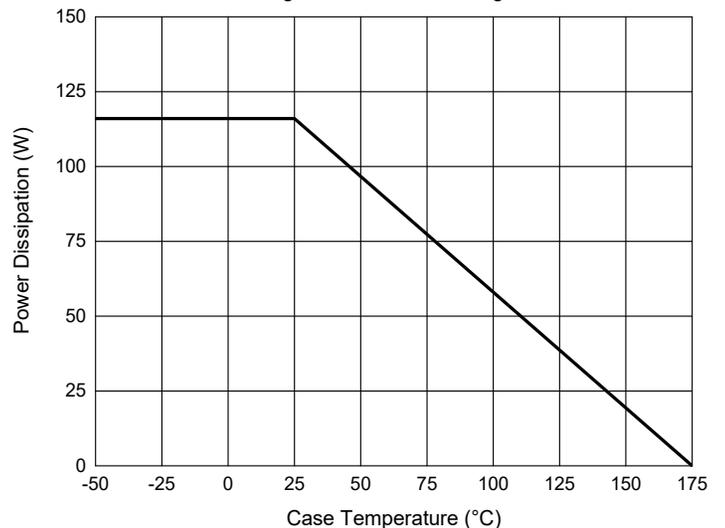


Fig. 18 - Power Derating



## Ordering Information

Device	Packing
SICBG160N120A-TP	800pcs/Reel

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